

Product Termination Notification

Product Group: SIL/Tue Jun 13, 2023/PTN-SIL-029-2023-REV-0



Conversion to Copper (Cu) Wire - SQ3456BEV

For further information, please contact your regional Vishay office.

CONTACT INFORMATION	
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Description of Change: The affected part number listed in this notification will be converted to a Copper wire material set. The new ordering code is SQ3456CEV-T1_GE3, which has the exact same product performance and fit as SQ3456BEV. There will be no change to the wafer fab or assembly location. There will be no changes to the parameters on the datasheet (reference: SQ3456CEV Doc # 62060 Rev.B).

Classification of Change: Standardization of materials

Expected Influence on Quality/Reliability/Performance: None

Part Numbers/Series/Families Affected: SQ3456BEV-T1_GE3

Vishay Brand(S): Vishay Siliconix

Time Schedule:

Last Time Buy Date: Wed Dec 20, 2023 Last Time Ship Date: Sun Jun 16, 2024

Sample Availability: Samples available on request

Product Identification: SQ3456CEV-T1_GE3

Qualification Data: Qualification data available on request

This PTN is considered approved, without further notification, unless we receive specific customer concerns before Sun Dec 17, 2023 or as specified by contract.

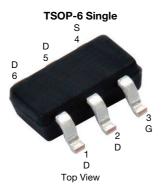
 $\textbf{Issued By:} \ Vishay \ Siliconix, business-americas@vishay.com$



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Automotive N-Channel 30 V (D-S) 175 °C MOSFET



Marking Code: 9Gxxx

PRODUCT SUMMARY	
V _{DS} (V)	30
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.035
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.052
I _D (A)	7.8
Configuration	Single

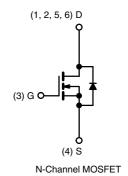
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3456CEV (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	30	V	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	1	7.8		
	T _C = 125 °C	I _D	4.5		
Continuous source current (diode conduction)		I _S	5	Α	
Pulsed drain current ^a		I _{DM}	31		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	10		
Single pulse avalanche energy	L = 0.1 min	E _{AS}	5	mJ	
Maximum power dissipation	T _C = 25 °C	В	4	W	
	T _C = 125 °C	P_{D}	1.3	VV	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL LIMIT		UNIT
Junction to ambient	PCB mount ^b	R_{thJA}	110	°C/W
Junction to foot (drain)	n to foot (drain)		38	C/VV

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR-4 material)



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SPECIFICATIONS (T _C = 25 °C, u	nless other	wise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		30	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 30 V	-	=.	1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	150		
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	10	=.	-	Α	
		V _{GS} = 10 V	I _D = 6 A	-	0.028	0.035		
Drain course on state registeres a	р	V _{GS} = 4.5 V	I _D = 4.9 A	-	0.036	0.052	0	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 6 A, T _J = 125 °C	-	-	0.054	Ω	
		V _{GS} = 10 V	I _D = 6 A, T _J = 175 °C	-	-	0.064		
Forward transconductance b	9 _{fs}	V_{DS}	= 15 V, I _D = 5 A	-	21	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = 15 V, f = 1 MHz	-	295	370	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		=.	73	85		
Reverse transfer capacitance	C _{rss}			-	25	35		
Total gate charge ^c	Q_g		10 V V _{DS} = 15 V, I _D = 6 A		6	10	nC	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V		=.	1.2	-		
Gate-drain charge ^c	Q _{gd}			-	1	-		
Gate resistance	R_g	f = 1 MHz		3.0	6.65	11	Ω	
Turn-on delay time ^c	t _{d(on)}			-	6	9		
Rise time ^c	t _r	V_{DD} = 15 V, R_L = 2.5 Ω $I_D \cong 6$ A, V_{GEN} = 10 V, R_g = 1 Ω		-	12	18	no	
Turn-off delay time ^c	t _{d(off)}			-	13	20	ns	
Fall time ^c	t _f			-	8	12		
Source-Drain Diode Ratings and Charact	teristics ^b							
Pulsed current ^a	I _{SM}				-	31	Α	
Forward voltage	V_{SD}	I _F = 3 A, V _{GS} = 0 V		-	0.8	1.1	V	
Body diode reverse recovery time	t _{rr}	I _F = 5 A, di/dt = 100 A/μs			10	20	ns	
Body diode reverse recovery charge	Q _{rr}				5	10	nC	
Reverse recovery fall time	ta			-	7	-	ns	
Reverse recovery rise time	t _b			-	3	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.88	-	Α	

Notes

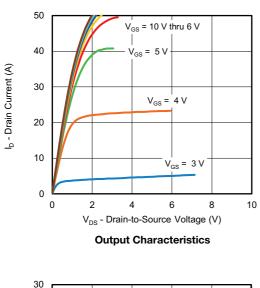
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

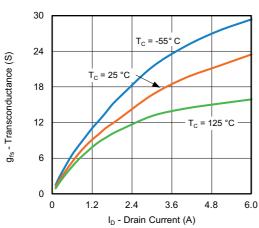
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



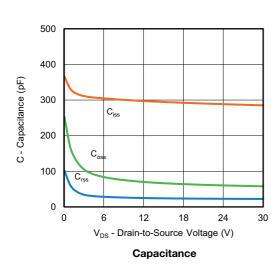


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

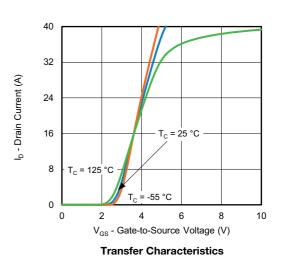


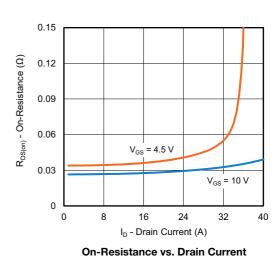


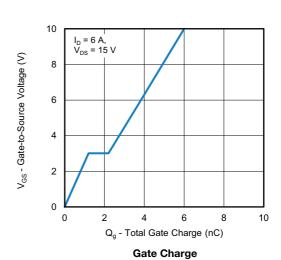
Transconductance



S23-0427-Rev. B, 05-Jun-2023

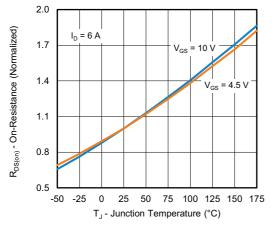




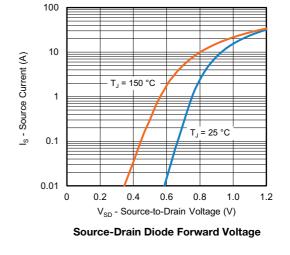


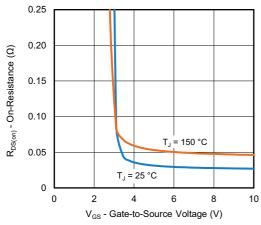


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

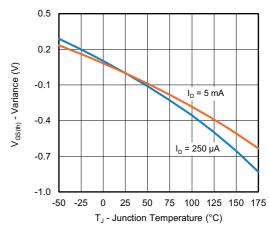


On-Resistance vs. Junction Temperature

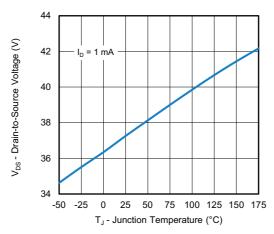




On-Resistance vs. Gate-to-Source Voltage



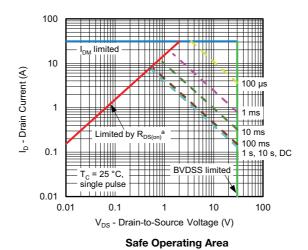
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

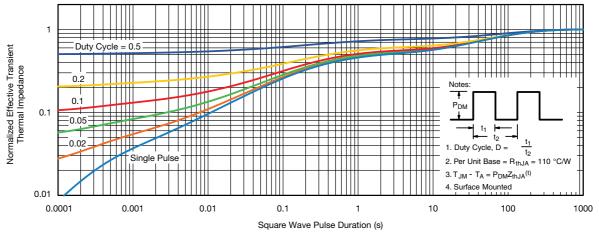
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Note

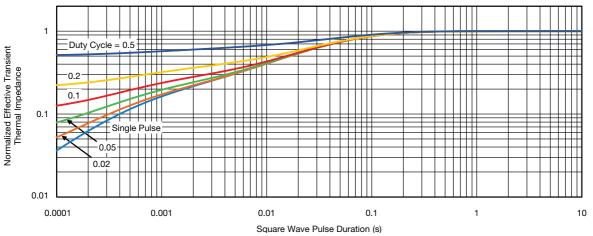
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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